ELSEVIER

Journal of Crystal Growth 146 (1994) 665–673

JOURNAL OF CRYSTAL GROWTH

Author index

Ahmed, M.U., E.D. Jones, J.B. Mullin and N.M. Stewart, Measurement of etch pit densities in diffused samples of CdTe 146 (1995) 136
Ajà, D., see Rossetto 146 (1995) 511
Akasaki, I. and H. Amano, Crystal growth of column III nitrides and their applications to short wavelength light emitters 146 (1995) 455
Allegretti, F., M. Inoue and T. Nishinaga, In-situ observation of GaAs selective epitaxy on GaAs (111)B substrates 146 (1995) 354
Alperovich, V.L., see Bolkhovityanov 146 (1995) 31
Amano, H., see Akasaki 146 (1995) 455
Asaka, N., see Hashimoto 146 (1995) 649
Astrova, E.V., see Chaldyshev 146 (1995) 246
Auld, J., see Jones 146 (1995) 503

Baba-Ali, N., see Novikov 146 (1995) 34
Bąk-Misiuk, J., see Grasza 146 (1995) 75
Baldus, A., A. Bett, U. Blieske, O.V. Sulima and W. Wettling, Etchback-regrowth process for AlGaAs/GaAs solar cell structures 146 (1995) 299
Baldus, A., A. Bett, O.V. Sulima and W. Wettling, Investigation of GaAs growth from Bi-based melts for solar cells 146 (1995) 305
Bauer, P., see Wirthl 146 (1995) 404
Becker, C.R., see Einfeldt 146 (1995) 427
Benz, K.W., see Kloess 146 (1995) 13
Benz, K.W., see Schwarz 146 (1995) 92
Benz, K.W., see Eiche 146 (1995) 98
Benz, K.W., see Laasch 146 (1995) 125
Benz, K.W., see Fiederle 146 (1995) 142
Benz, K.W., see Danilewsky 146 (1995) 171
Berbezier, I., see Natoli 146 (1995) 444
Bergunde, T., D. Gutsche, L. Kadinski, Yu. Makarov and M. Weyers, Transport and reaction behaviour in Aix-2000 Planetary metalorganic vapour phase epitaxy reactor 146 (1995) 564
Bett, A., see Baldus 146 (1995) 299
Bett, A., see Baldus 146 (1995) 305
Biao, Y., see Nason 146 (1995) 23
Birecki, H., see Helbing 146 (1995) 599
Blieske, U., see Baldus 146 (1995) 299
Böbel, F.G., see Ritter 146 (1995) 119
Bobrovnikova, I.A., see Chaldyshev 146 (1995) 246
Bock, A., see Spika 146 (1995) 521
Bolkhovityanov, Yu.B., V.L. Alperovich, A.S. Jaroshevich, N.V. Nomerotsky, A.G. Paulish, A.S. Terekhov and E.M. Trukhanov, Liquid phase epitaxial growth of elastically strained InGaAsP layers for spin-polarized electron sources 146 (1995) 31
Booker, G.R., P.C. Klipstein, M. Lakrimi, S. Lyapin, N.J. Mason, I.J. Murgatroyd, R.J. Nicholas, T.-Y. Seong, D.M. Symons and P.J. Walker, Growth of InAs/GaSb strained layer superlattices.II 146 (1995) 495
Böttcher, K. and H. Hartmann, Zinc selenide single crystal growth by chemical transport reactions 146 (1995) 53
Brebick, R.F., see Sha 146 (1995) 42
Breitkopf, Th., see Grün 146 (1995) 414
Brennan, S., see Kisker 146 (1995) 104
Brinkman, A.W., see Hallam 146 (1995) 604
Brunthaler, G., see Ferreira 146 (1995) 418
Bullough, T.J., see Joyce 146 (1995) 394
Bullough, T.J., see Pfeffer 146 (1995) 399
Burger, A., see Nason 146 (1995) 23

Cadoret, R., α-Mercuric iodide crystal growth by physical vapour transport 146 (1995) 9
Camporese, A., see Rossetto 146 (1995) 511
Capelletti, R., see Zha 146 (1995) 29
Chaldyshev, V.V., E.V. Astrova, A.A. Lebedev, I.A. Bobrovnikova, N.A. Chernov, O.M. Ivleva, L.G. Lavrentieva, I.V. Teterkina and M.D. Vilisova, Vapour phase epitaxial grown GaAs films with a very low deep level concentration 146 (1995) 246
Chen, J.-X., see Chen 146 (1995) 624
Chen, Y.-F., J.-X. Chen, L. Shun, T. Yu, P. Li, N.-B. Ming and L.-J. Shi, Preparation of epitaxial $PbTiO_3$ thin films by metalorganic vapor phase epitaxy under reduced pressure 146 (1995) 624
Cheng, T.S., see Novikov 146 (1995) 34
Chernov, N.A., see Chaldyshev 146 (1995) 246
Chevy, A., see Lang 146 (1995) 439
Cowache, P., see Kampmann 146 (1995) 256

Danilewsky, A.N., Y. Okamoto, T. Nishinaga and K.W. Benz, Theoretical study of macrostep stability under temperature gradient 146 (1995) 171
Derrien, J., see Natoli 146 (1995) 444
DeVries, M., see Schieber 146 (1995) 15
DiCarolis, S.A., see Helbing 146 (1995) 599
Dittrich, H., see Zweigart 146 (1995) 233
Durose, K., see Hallam 146 (1995) 604
Durst, F., L. Kadinski and M. Schäfer, A multigrid solver for fluid flow and mass transfer coupled with grey-body surface radiation for the numerical simulation of chemical vapor deposition processes 146 (1995) 202

Eaves, L., see Novikov 146 (1995) 34
Ebe, H., see Nishino 146 (1995) 619
Ebling, D., see Eiche 146 (1995) 98
Ebling, D., see Fiederle 146 (1995) 142
Egawa, T., see Fujita 146 (1995) 384
Egorov, A.V., see Golubev 146 (1995) 277
Eiche, C., see Schwarz 146 (1995) 92
Eiche, C., W. Joerger, M. Fiederle, D. Ebling, R. Schwarz and K.W. Benz, Investigation of CdTe:Cl grown from the vapour phase under microgravity conditions with time dependent charge measurements and photoinduced current transient spectroscopy 146 (1995) 98
Eiche, C., see Laasch 146 (1995) 125
Eiche, C., see Fiederle 146 (1995) 142
Einfeldt, S., U. Lunz, H. Heinke, C.R. Becker and G. Landwehr, Molecular beam epitaxial growth and segregation of $Hg_{1-x}Zn_xSe$ alloys 146 (1995) 427
Ekawa, M., see Fujii 146 (1995) 475
Ellmer, K., see Thomas 146 (1995) 63
Ellmer, K., see Tomm 146 (1995) 271

Faschinger, W., Doping of wide gap II–VI compounds 146 (1995) 8
Faschinger, W., see Ferreira 146 (1995) 418
Favaro, M.L., see Rossetto 146 (1995) 511
Feigelson, R.S., see Helbing 146 (1995) 599
Ferreira, S.O., H. Sitter, W. Faschinger, R. Krump and G. Brunthaler, Type I–type II band offset transition of the ZnMgSe–ZnTe system 146 (1995) 418
Fiechter, S., see Thomas 146 (1995) 63
Fiechter, S., see Tomm 146 (1995) 271
Fiederle, M., see Schwarz 146 (1995) 92
Fiederle, M., see Eiche 146 (1995) 98
Fiederle, M., see Laasch 146 (1995) 125
Fiederle, M., D. Ebling, C. Eiche, P. Hug, W. Joerger, M. Laasch, R. Schwarz, M. Salk and K.W. Benz, Studies of the compensation mechanism in CdTe grown from the vapour phase 146 (1995) 142
Finders, J., see Hövel 146 (1995) 515
Foxon, C.T., see Novikov 146 (1995) 34
Franzheld, R., see Rossetto 146 (1995) 511
Franzosi, P., see Zha 146 (1995) 29
Fujibayashi, K., see Tabuchi 146 (1995) 148
Fujii, N., see Kizuki 146 (1995) 527
Fujii, T., M. Ekawa and S. Yamazaki, A theory for metalorganic vapor phase epitaxial selective growth on planar patterned substrates 146 (1995) 475
Fujii, T. and S. Yamazaki, A new lattice relaxation mode in InGaAs on GaAs 146 (1995) 489
Fujita, K., K. Nitatori, M. Hosoda, T. Egawa, Y. Niwano, T. Jimbo, M. Umeno and T. Watanabe, Molecular beam epitaxial growth of AlGaAs p–n junctions on GaAs(111)A substrates using only silicon dopant 146 (1995) 384
Fujita, K., see Nitatori 146 (1995) 389
Fujiwara, Y., S. Furuta, K. Makita, Y. Ito, Y. Nonogaki and Y. Takeda, Drastic effects of hydrogen flow rate on growth characteristics and electrical/optical properties of InP grown by organometallic vapour phase epitaxy with TMIn and TBP 146 (1995) 544
Fukagawa, W., see Ohshita 146 (1995) 188
Fukui, T., J. Ishizaki, S. Hara, J. Motohisa and H. Hasegawa, Multiatomic step formation mechanism of metalorganic vapor phase epitaxial grown GaAs vicinal surfaces and its application to quantum well wires 146 (1995) 183
Funaki, M., see Hallam 146 (1995) 604
Fuoss, P.H., see Kisker 146 (1995) 104
Furuta, S., see Fujiwara 146 (1995) 544

Gavryushin, V., see Kazlauskas 146 (1995) 59
Ge, Y.R., see Wiedemeier 146 (1995) 61
Gerlach, H., see Grün 146 (1995) 414
Gheyas, S.I., see Ogata 146 (1995) 587
Giersig, M., see Löher 146 (1995) 408
Gillies, D.C., see Sha 146 (1995) 42
Gimmnich, P., see Spika 146 (1995) 521
Gladkov, P., E. Monova and J. Weber, Liquid phase epitaxy and photoluminescence characterization of p-type GaSb layers grown from Bi based melts 146 (1995) 319
Göbel, E.O., see Spika 146 (1995) 521
Golubev, L.V., A.V. Egorov, S.V. Novikov and Yu.V. Shmartsev, Liquid phase electroepitaxy of III–V semiconductors 146 (1995) 277
Gonda, T., see Gotoh 146 (1995) 198
Goorsky, M., see Schieber 146 (1995) 15
Gorochov, O., see Kuhn 146 (1995) 58
Gösele, U., see Kobayashi 146 (1995) 533

Gotoh, Y., A. Horii, H. Kawanowa, M. Kamei, H. Yumoto and T. Gonda, Growth mechanism of a Ag crystal particle containing a twin plane grown on a Mo(110) surface 146 (1995) 198
Grasza, K., Bulk vapour growth of CdTe 146 (1995) 65
Grasza, K., Effect of temperature field on growth stability 146 (1995) 69
Grasza, K., E. Janik, A. Mycielski and J. Bąk-Misiuk, The optimal temperature profile in crystal growth from the vapour 146 (1995) 75
Grasza, K., see Laasch 146 (1995) 125
Greiling, A., see Spika 146 (1995) 521
Griesche, J., see Hoffmann 146 (1995) 422
Grün, M., H. Gerlach, Th. Breitkopf, M. Hetterich, A. Reznitsky, H. Kalt and C. Klingshirn, Epitaxial growth and photoluminescence of hexagonal $CdS_{1-x}Se_x$ alloy 146 (1995) 414
Guo, Q., H. Ogawa and A. Yoshida, Growth of $Al_xIn_{1-x}N$ single crystal films by microwave-excited metalorganic vapor phase epitaxy 146 (1995) 462
Gurskii, A.L., K. Vakarelska, W. Taudt, B. Wachtendorf, J. Söllner, A. Wahid and M. Heuken, Oxygen and tellurium impurities in zinc selenide grown by metalorganic vapour phase epitaxy 146 (1995) 592
Gutsche, D., see Bergunde 146 (1995) 564
Gyuro, I., see Prost 146 (1995) 538

Hallam, T.D., Ş. Oktik, M. Funaki, C. Moore, A.W. Brinkman, K. Durose and B.K. Tanner, Uniformity in (Hg, Mn)Te films grown by metalorganic vapour phase epitaxy 146 (1995) 604
Hamano, T., see Matsushige 146 (1995) 641
Hara, S., see Fukui 146 (1995) 183
Harada, J., see Tabuchi 146 (1995) 148
Hartmann, H., see Böttcher 146 (1995) 53
Hasegawa, H., see Fukui 146 (1995) 183
Hashimoto, S., T. Ogawa, N. Asaka, S. Isoda and T. Kobayashi, Pseudomorphic vanadyl-phthalocyanine and its stable orientation on KBr 146 (1995) 649
Heimbrodt, W., see Hoffmann 146 (1995) 422
Heime, K., see Hövel 146 (1995) 515
Heinke, H., see Einfeldt 146 (1995) 427
Heinze, M., see Hofmann 146 (1995) 214
Helbing, R., see Kuhn 146 (1995) 58
Helbing, R., H. Birecki, S.A. DiCarolis, R.S. Feigelson and R. Hiskes, Growth of CaS thin films by solid source metalorganic chemical vapor deposition 146 (1995) 599
Herman, M.A., see Sadowski 146 (1995) 449
Hertel, B., see Ritter 146 (1995) 119
Hetterich, M., see Grün 146 (1995) 414
Heuken, M., Metalorganic vapor phase epitaxy of wide-gap II–VI semiconductors for optoelectronic applications: current status and future trends 146 (1995) 57
Heuken, M., see Gurskii 146 (1995) 592
Hillmer, H., R. Lösch, W. Schlapp and A. Pöcker, Characterization of high-quality molecular beam epitaxial grown In_xAl_z-$Ga_{1-x-z}As$/ $In_yAl_uGa_{1-u-y}As$/ InP heterostructures 146 (1995) 159
Hiskes, R., see Helbing 146 (1995) 599
Ho, I.H., see Su 146 (1995) 558
Hoffmann, N., J. Griesche, W. Heimbrodt, V. Weinhold and K. Jacobs, Reflection high-energy electron diffraction controlled growth of ZnSe/(Zn, Mn)Se quantum well structures 146 (1995) 422
Hofmann, D., M. Heinze, A. Winnacker, F. Durst, L. Kadinski, P. Kaufmann, Yu. Makarov and M. Schäfer, On the sublimation growth of SiC bulk crystals: development of a numerical process model 146 (1995) 214
Hooper, S.E., see Novikov 146 (1995) 34
Höpfner, C., see Thomas 146 (1995) 63
Horii, A., see Gotoh 146 (1995) 198
Horiuchi, T., see Matsushige 146 (1995) 641
Hoshino, A., S. Isoda, H. Kurata and T. Kobayashi, Precise determination of the epitaxial orientation of a monomolecular layer organic film by scanning tunneling microscopy 146 (1995) 636
Hosoda, M., see Fujita 146 (1995) 384
Hövel, R., E. Steimetz, St. Mannheim, V. Sommer, J. Woitok, J. Finders and K. Heime, The n-type doping of GaAs/ $Al_xGa_{1-x}As$ and growth of two-dimensional electron gas structures with DEAlH–NMe_3 as Al source 146 (1995) 515
Huang, M.-H., see Huang 146 (1995) 659
Huang, Y. and M.-H. Huang, Liquid phase epitaxy of $Bi_2Sr_2CaCu_2O_x$ superconductor from a $BiO_{1.5}$–SrO–CaO–CuO solution 146 (1995) 659
Hug, P., see Fiederle 146 (1995) 142
Hutchins, M.A., see Wiedemeier 146 (1995) 61

Ikejiri, M., see Ogata 146 (1995) 587
Ikuta, K., see Inoue 146 (1995) 379
Inoue, M., see Yano 146 (1995) 349
Inoue, M., see Allegretti 146 (1995) 354
Inoue, N., Elementary processes in molecular beam epitaxy studied by in-situ scanning electron microscopy 146 (1995) 334
Inoue, N., K. Ikuta, M. Shinohara and J. Osaka, Interface structures in GaAs/ Al(Ga)As quantum wells controlled by metalorganic vapor phase epitaxy and molecular beam epitaxy 146 (1995) 379

Inoue, Y., see Saitoh 146 (1995) 359
Ishizaki, J., see Fukui 146 (1995) 183
Isobe, S., see Muranoi 146 (1995) 49
Isoda, S., see Hoshino 146 (1995) 636
Isoda, S., see Hashimoto 146 (1995) 649
Ito, W., Y. Yoshida, S. Mahajan and T. Morishita, Effects of a lattice matching in hetero-epitaxially grown *a*-axis YBCO films on superconductivity 146 (1995) 655
Ito, Y., see Fujiwara 146 (1995) 544
Ivleva, O.M., see Chaldyshev 146 (1995) 246
Izawa, M., see Takiguchi 146 (1995) 645

Jacobs, K., see Hoffmann 146 (1995) 422
Jaegermann, W., see Löher 146 (1995) 408
Jaegermann, W., see Lang 146 (1995) 439
James, R.B., see Schieber 146 (1995) 15
Janik, E., see Grasza 146 (1995) 75
Jaroshevich, A.S., see Bolkhovityanov 146 (1995) 31
Jenkins, L.C., see Novikov 146 (1995) 34
Jimbo, T., see Fujita 146 (1995) 384
Jimbo, T., see Soga 146 (1995) 554
Joerger, W., see Schwarz 146 (1995) 92
Joerger, W., see Eiche 146 (1995) 98
Joerger, W., see Laasch 146 (1995) 125
Joerger, W., see Fiederle 146 (1995) 142
Johnston, D., see Novikov 146 (1995) 34
Jones, A.C., see Pfeffer 146 (1995) 399
Jones, A.C., S.A. Rushworth and J. Auld, Recent developments in metalorganic precursors for metalorganic chemical vapour deposition 146 (1995) 503
Jones, E.D., see Ahmed 146 (1995) 136
Joyce, T.B., T.J. Bullough and S. Westwater, In-situ monitoring of carbon doped GaAs and of periodic carbon doped GaAs/AlAs structures grown by chemical beam epitaxy 146 (1995) 394
Joyce, T.B., see Pfeffer 146 (1995) 399

Kadinski, L., see Durst 146 (1995) 202
Kadinski, L., Yu. Makarov, M. Schäfer, M.G. Vasil'ev and V.S. Yuferev, Development of advanced mathematical models for numerical calculations of radiative heat transfer in metalorganic chemical vapour deposition reactors 146 (1995) 209
Kadinski, F. Durst. L., see Hofmann 146 (1995) 214
Kadinski, L., see Bergunde 146 (1995) 564
Kaldis, E., see Rossberg 146 (1995) 112
Kalt, H., see Grün 146 (1995) 414
Kamei, H., see Tabuchi 146 (1995) 148
Kamei, M., see Gotoh 146 (1995) 198
Kampmann, A., P. Cowache, B. Mokili, D. Lincot and J. Vedel, Characterization of ⟨111⟩ cadmium telluride electrodeposited on cadmium sulphide 146 (1995) 256
Kanbe, N., see Muranoi 146 (1995) 49
Karpov, S.Yu., V.E. Myachin and Yu.V. Pogorelsky, Time-resolved reflection high energy electron diffraction study of dynamical surface processes during molecular beam epitaxy of GaAs and AlAs 146 (1995) 344
Kassing, R., see Spika 146 (1995) 521
Kaufmann, P., see Hofmann 146 (1995) 214
Kawanowa, H., see Gotoh 146 (1995) 198
Kazlauskas, A., V. Gavryushin, G. Račuikaitis and O. Makienko, Stoichiometry of CdS crystals and their optical and lasing properties 146 (1995) 59
Kern, R. and P. Müller, Three-dimensional towards two-dimensional coherent epitaxy initiated by surfactants 146 (1995) 193
Kessler, J., see Zweigart 146 (1995) 233
Kim, M.-S., Y. Kim, M.-S. Lee, Y.J. Park, S.-I. Kim and S.-K. Min, Growth behavior on V-grooved high Miller index GaAs substrates by metalorganic chemical vapor deposition 146 (1995) 482
Kim, S.-I., see Kim 146 (1995) 482
Kim, Y., see Kim 146 (1995) 482
Kimata, M., T. Suzuki, K. Shimomura and M. Yano, Interdiffusion of In, Te at the interface of molecular beam epitaxial grown CdTe/InSb heterostructures 146 (1995) 433
Kisker, D.W., G.B. Stephenson, P.H. Fuoss and S. Brennan, Characterization of vapor phase growth using X-ray techniques 146 (1995) 104
Kizuki, H., N. Fujii, M. Miyashita, Y. Mihashi and S. Takamiya, Reduction of interface contamination in regrown GaAs on AlGaAs using a novel two-step HCl gas etching process 146 (1995) 527
Klein, A., see Lang 146 (1995) 439
Klingshirn, C., see Grün 146 (1995) 414
Klipstein, P.C., see Booker 146 (1995) 495
Kloess, G., M. Laasch, R. Schwarz and K.W. Benz, Stress birefringence and microinclusions in sublimation-grown bulk CdTe 146 (1995) 13
Knauer, A., E. Richter and M. Weyers, Effects of storage time of epi-ready InP:Fe substrates on the quality of metalorganic vapour phase epitaxial grown InP 146 (1995) 549
Kobayashi, A., see Ohshita 146 (1995) 188
Kobayashi, T., K. Kurishima and U. Gösele, Growth temperature dependence of Zn diffusion in InP/InGaAs heterojunction bipolar transistor structures grown by metalorganic chemical vapor deposition 146 (1995) 533
Kobayashi, T., see Hoshino 146 (1995) 636
Kobayashi, T., see Hashimoto 146 (1995) 649
Koukitu, A., N. Takahashi, Y. Miura and H. Seki, In situ gravimetric monitoring of arsenic desorption in GaAs atomic layer epitaxy 146 (1995) 239

Koukitu, A., N. Takahashi and H. Seki, In situ monitoring of the growth process in GaAs atomic layer epitaxy by gravimetric and optical methods 146 (1995) 467
Kreshchuk, A.M., S.V. Novikov, T.A. Polyanskaya, I.G. Savel'ev and A.Ya. Shik, Quantum transport effects in a two-dimensional electron gas as a tool for the investigation of heterointerfaces 146 (1995) 153
Krump, R., see Ferreira 146 (1995) 418
Kuhn, W.S., R. Helbing, B. Qu'Hen and O. Gorochov, Thermal dissociation of ditertiarybutylselenide and methylallylselenide and its impact on the growth of ZnSe by metalorganic vapour phase epitaxy 146 (1995) 58
Kumamoto, T., see Tabuchi 146 (1995) 148
Kurata, H., see Hoshino 146 (1995) 636
Kurishima, K., see Kobayashi 146 (1995) 533

Laasch, M., see Kloess 146 (1995) 13
Laasch, M., R. Schwarz, W. Joerger, C. Eiche, M. Fiederle, K.W. Benz and K. Grasza, Characterization of cadmium telluride crystals grown by different techniques from the vapour phase 146 (1995) 125
Laasch, M., see Fiederle 146 (1995) 142
Lacklison, D.E., see Novikov 146 (1995) 34
Lakner, H., see Prost 146 (1995) 538
Lakrimi, M., see Booker 146 (1995) 495
Landwehr, G., see Einfeldt 146 (1995) 427
Lang, O., A. Klein, R. Schlaf, T. Löher, C. Pettenkofer, W. Jaegermann and A. Chevy, InSe/GaSe heterointerfaces prepared by Van der Waals epitaxy 146 (1995) 439
Lanig, P., see Rupp 146 (1995) 37
Lavrentieva, L.G., see Chaldyshev 146 (1995) 246
Lebedev, A.A., see Chaldyshev 146 (1995) 246
Lee, M.-S., see Kim 146 (1995) 482
Lehoczky, S.L., see Sha 146 (1995) 42
Li, P., see Chen 146 (1995) 624
Lincot, D., see Kampmann 146 (1995) 256
Lindner, A., see Prost 146 (1995) 538
Liu, H.-C., see Sha 146 (1995) 42
Liu, Q., see Prost 146 (1995) 538
Löher, T., Y. Tomm, C. Pettenkofer, M. Giersig and W. Jaegermann, Epitaxial films of the 3D semiconductor CdS on the 2D layered substrate MX_2 prepared by Van der Waals epitaxy 146 (1995) 408
Löher, T., see Lang 146 (1995) 439
Lorberth, J., see Spika 146 (1995) 521
Lösch, R., see Hillmer 146 (1995) 159
Lunz, U., see Einfeldt 146 (1995) 427
Lyapin, S., see Booker 146 (1995) 495

Magerl, A., see Rossberg 146 (1995) 112
Mahajan, S., see Ito 146 (1995) 655
Makarov, Yu., see Kadinski 146 (1995) 209
Makarov, Yu., see Hofmann 146 (1995) 214
Makarov, Yu., see Bergunde 146 (1995) 564
Makienko, O., see Kazlauskas 146 (1995) 59
Makita, K., see Fujiwara 146 (1995) 544
Mannheim, St., see Hövel 146 (1995) 515
Mason, N.J., see Booker 146 (1995) 495
Matsumoto, K., see Schönherr 146 (1995) 227
Matsushige, K., T. Hamano and T. Horiuchi, Atomic force microscopy observation of the epitaxial growth of organic molecules 146 (1995) 641
Mihashi, Y., see Kizuki 146 (1995) 527
Min, S.-K., see Kim 146 (1995) 482
Ming, N.-B., see Chen 146 (1995) 624
Miura, Y., see Koukitu 146 (1995) 239
Miwa, K. and T. Nishinaga, Theoretical studies of step edge supersaturation and its As/Ga flux dependence in molecular beam epitaxy of GaAs on vicinal surfaces 146 (1995) 177
Miyashita, M., see Kizuki 146 (1995) 527
Mokili, B., see Kampmann 146 (1995) 256
Möller, H., see Ritter 146 (1995) 119
Monova, E., see Gladkov 146 (1995) 319
Moore, C., see Hallam 146 (1995) 604
Morishita, T., see Ito 146 (1995) 655
Motohisa, J., see Fukui 146 (1995) 183
Müller, P., see Kern 146 (1995) 193
Mullin, J.B., see Ahmed 146 (1995) 136
Murakami, S., see Nishino 146 (1995) 619
Muranoi, T., T. Shiohara, A. Sotokawa, H. Yoshida, S. Isobe and N. Kanbe, Gas effect on transport rates of ZnSe in closed ampoules 146 (1995) 49
Murgatroyd, I.J., see Booker 146 (1995) 495
Myachin, V.E., see Karpov 146 (1995) 344
Mycielski, A., see Grasza 146 (1995) 75

Nabetani, Y., N. Yamamoto, T. Tokuda and A. Sasaki, Island formation of InAs grown on GaAs 146 (1995) 363
Nadeneau, V., T. Walter and H.W. Schock, Growth of $CuInTe_2$ polycrystalline thin films 146 (1995) 251
Nagashima, S. and I. Otsuka, Surface topography of epitaxial Au(111) films deposited on MoS_2 146 (1995) 266
Naritsuka, S. and T. Nishinaga, Epitaxial lateral overgrowth of InP by liquid phase epitaxy 146 (1995) 314
Nason, D., Y. Biao and A. Burger, Optical methods for measuring iodine vapor during mercuric iodide crystal growth by physical vapor transport 146 (1995) 23
Natoli, J.Y., I. Berbezier, A. Ronda and J. Derrien, Chemical beam epitaxy of iron disilicide on silicon 146 (1995) 444
Nicholas, R.J., see Booker 146 (1995) 495

Nishijima, Y., see Nishino 146 (1995) 619
Nishinaga, T., see Danilewsky 146 (1995) 171
Nishinaga, T., see Miwa 146 (1995) 177
Nishinaga, T., see Naritsuka 146 (1995) 314
Nishinaga, T., Elementary growth process of molecular beam epitaxy 146 (1995) 326
Nishinaga, T., see Allegretti 146 (1995) 354
Nishinaga, T., see Shen 146 (1995) 374
Nishino, H., S. Murakami, H. Ebe and Y. Nishijima, Reduction of autodoped gallium concentration in HgCdTe layers on GaAs grown by metalorganic vapor phase epitaxy 146 (1995) 619
Nishio, M., see Ogata 146 (1995) 587
Nitatori, K., see Fujita 146 (1995) 384
Nitatori, K., K. Fujita and T. Watanabe, High-quality Si-doped GaAs/$In_{0.1}Al_{0.9}$-As alternating $\lambda/4$ layers grown on a slightly misorientated GaAs(111)A substrate by molecular beam epitaxy 146 (1995) 389
Niwano, Y., see Fujita 146 (1995) 384
Nohavica, D. and J. Oswald, Preparation of periodic structures by meander type liquid phase epitaxy 146 (1995) 287
Nomerotsky, N.V., see Bolkhovityanov 146 (1995) 31
Nonogaki, Y., see Fujiwara 146 (1995) 544
Novikov, S.V., C.T. Foxon, T.S. Cheng, T.L. Tansley, J.W. Orton, D.E. Lacklison, D. Johnston, N. Baba-Ali, S.E. Hooper, L.C. Jenkins and L. Eaves, Auger investigation of group III nitride films grown by molecular beam epitaxy 146 (1995) 34
Novikov, S.V., see Kreshchuk 146 (1995) 153
Novikov, S.V., see Golubev 146 (1995) 277

Ogata, T., S.I. Gheyas, M. Ikejiri, H. Ogawa and M. Nishio, Synchrotron radiation excited growth of ZnTe using metalorganic sources 146 (1995) 587
Ogawa, H., see Guo 146 (1995) 462
Ogawa, H., see Ogata 146 (1995) 587
Ogawa, T., see Hashimoto 146 (1995) 649
Ohshima, N., see Saitoh 146 (1995) 359
Ohshita, Y., W. Fukagawa and A. Kobayashi, Effects of adsorbates on step coverage in TiN chemical vapor deposition 146 (1995) 188
Okamoto, Y., see Danilewsky 146 (1995) 171
Oktik, Ş., see Hallam 146 (1995) 604
Orton, J.W., see Novikov 146 (1995) 34
Osaka, J., see Inoue 146 (1995) 379
Oswald, J., see Nohavica 146 (1995) 287
Otsuka, I., see Nagashima 146 (1995) 266

Pak, K., see Saitoh 146 (1995) 359
Palosz, W., see Sha 146 (1995) 42
Paorici, C., see Zha 146 (1995) 29
Park, Y.J., see Kim 146 (1995) 482
Paulish, A.G., see Bolkhovityanov 146 (1995) 31
Pettenkofer, C., see Löher 146 (1995) 408
Pettenkofer, C., see Lang 146 (1995) 439
Pfeffer, T.L., T.J. Bullough, T.B. Joyce and A.C. Jones, The use of diethylsulphide for the doping of $Al_xGa_{1-x}As$ grown by chemical beam epitaxy 146 (1995) 399
Piechotka, M., Mechanism of vapour growth and defect formation in large mercuric iodide crystals 146 (1995) 1
Piechotka, M., see Rossberg 146 (1995) 112
Ploog, K.H., see Trampert 146 (1995) 368
Plotz, W.M., see Tagwerker 146 (1995) 22
Pöcker, A., see Hillmer 146 (1995) 159
Pogorelsky, Yu.V., see Karpov 146 (1995) 344
Polyanskaya, T.A., see Kreshchuk 146 (1995) 153
Prost, W., F. Scheffer, Q. Liu, A. Lindner, H. Lakner, I. Gyuro and F.J. Tegude, Metalorganic vapor phase epitaxial grown heterointerfaces to GaInP with group-III and group-V exchange 146 (1995) 538

Qu'Hen, B., see Kuhn 146 (1995) 58

Račuikaitis, G., see Kazlauskas 146 (1995) 59
Razzetti, C., see Zha 146 (1995) 29
Reznitsky, A., see Grün 146 (1995) 414
Richter, E., see Knauer 146 (1995) 549
Ritter, G., B. Tillack, M. Weidner, P. Zaumseil, F.G. Böbel, B. Hertel and H. Möller, In-situ observation of chemical vapour deposition growth of epitaxial SiGe thin films by reflection supported pyrometric interferometry 146 (1995) 119
Ronda, A., see Natoli 146 (1995) 444
Rossberg, A., M. Piechotka, A. Magerl, E. Steichele, G. Wetzel and E. Kaldis, A study of structural defects in vapour grown α-HgI_2 single crystals by γ-ray diffraction 146 (1995) 112
Rossetto, G., R. Franzheld, A. Camporese, M.L. Favaro, G. Torzo, D. Ajà and P. Zanella , A new precursor for epitaxial growth of indium based semiconductors 146 (1995) 511
Roth, M., see Schieber 146 (1995) 15
Rupp, R., P. Lanig, J. Völkl and D. Stephani, First results on silicon carbide vapour phase epitaxy growth in a new type of vertical low pressure chemical vapour deposition reactor 146 (1995) 37
Rushworth, S.A., see Jones 146 (1995) 503

Sadowski, J. and M.A. Herman, Hard heteroepitaxy of molecular beam epitaxial grown PbTe on off oriented GaAs(100) substrates 146 (1995) 449
Saito, Y., see Uwaha 146 (1995) 164

Saitoh, I., K. Pak, Y. Inoue, N. Ohshima and H. Yonezu, A study on in-situ maskless selective epitaxy of GaAs by a low-energy Ga focused ion beam with an As_4 molecular beam 146 (1995) 359
Sakuraba, Y., see Tabuchi 146 (1995) 148
Salk, M., see Fiederle 146 (1995) 142
Salzmann, A., see Spika 146 (1995) 521
Sasaki, A., see Nabetani 146 (1995) 363
Sato, K., see Takiguchi 146 (1995) 645
Sato, M., see Uwaha 146 (1995) 164
Sato, S., see Sato 146 (1995) 262
Sato, Y. and S. Sato, Influence of growth rates on properties of InN thin films 146 (1995) 262
Savel'ev, I.G., see Kreshchuk 146 (1995) 153
Schäfer, M., see Durst 146 (1995) 202
Schäfer, M., see Kadinski 146 (1995) 209
Schäfer, M., see Hofmann 146 (1995) 214
Scheffer, F., see Prost 146 (1995) 538
Schieber, M., M. Roth, H. Yao, M. DeVries, R.B. James and M. Goorsky, Bulk and surface stoichiometry of vapor grown mercuric iodide crystals 146 (1995) 15
Schieck, R., see Tomm 146 (1995) 271
Schlaf, R., see Lang 146 (1995) 439
Schlapp, W., see Hillmer 146 (1995) 159
Schmid, D., see Zweigart 146 (1995) 233
Schock, H.W., see Zweigart 146 (1995) 233
Schock, H.W., see Nadeneau 146 (1995) 251
Schönherr, E., K. Matsumoto and M. Wojnowski, Growth of C_{60} crystals from the vapor phase 146 (1995) 227
Schwarz, R., see Kloess 146 (1995) 13
Schwarz, R., W. Joerger, C. Eiche, M. Fiederle and K.W. Benz, Closed tube vapour growth of CdTe:V and CdTe:Ti and its characterization 146 (1995) 92
Schwarz, R., see Eiche 146 (1995) 98
Schwarz, R., see Laasch 146 (1995) 125
Schwarz, R., see Fiederle 146 (1995) 142
Seki, H., see Koukitu 146 (1995) 239
Seki, H., see Koukitu 146 (1995) 467
Seong, T.-Y., see Booker 146 (1995) 495
Šestáková, V. and B. Štěpánek, Doping of GaSb single crystals with various elements 146 (1995) 87
Sha, Y.-G., C.-H. Su, W. Palosz, M.P. Volz, D.C. Gillies, F.R. Szofran, S.L. Lehoczky, H.-C. Liu and R.F. Brebick, Mass flux of ZnSe by physical vapor transport 146 (1995) 42
Sha, Y.-G., see Wiedemeier 146 (1995) 61
Shen, X.Q. and T. Nishinaga, Inter-surface diffusion of In on (111)A-(001) InAs nonplanar substrates in molecular beam epitaxy 146 (1995) 374
Shi, L.-J., see Chen 146 (1995) 624
Shik, A.Ya., see Kreshchuk 146 (1995) 153
Shimomura, K., see Kimata 146 (1995) 433
Shinohara, M., see Inoue 146 (1995) 379
Shiohara, T., see Muranoi 146 (1995) 49
Shmartsev, Yu.V., see Golubev 146 (1995) 277
Shun, L., see Chen 146 (1995) 624
Sitter, H., see Tagwerker 146 (1995) 22
Sitter, H., see Wirthl 146 (1995) 404
Sitter, H., see Ferreira 146 (1995) 418
Soga, T., T. Jimbo and M. Umeno, Growth and characterization of two-dimensional GaP on Si by metalorganic chemical vapor deposition 146 (1995) 554
Söllner, J., see Gurskii 146 (1995) 592
Sommer, V., see Hövel 146 (1995) 515
Sotokawa, A., see Muranoi 146 (1995) 49
Spika, Z., G. Zimmermann, W. Stolz, E.O. Göbel, P. Gimmnich, J. Lorberth, A. Greiling, A. Salzmann, S. Weiß, U. Sudjadi, A. Bock and R. Kassing, Investigations on deep traps in GaAs and $(Al_xGa_{1-x})As$ bulk layers grown by metalorganic vapour-phase epitaxy using the new alternative arsenic precursor diethyl-tert-butylarsin 146 (1995) 521
Steichele, E., see Rossberg 146 (1995) 112
Steimetz, E., see Hövel 146 (1995) 515
Steiner, B. and G. Wagner, Silicon layers on polycrystalline silicon substrates – influence of growth parameters during liquid phase epitaxy 146 (1995) 293
Štěpánek, B., see Šestáková 146 (1995) 87
Stephani, D., see Rupp 146 (1995) 37
Stephenson, G.B., see Kisker 146 (1995) 104
Stewart, N.M., see Ahmed 146 (1995) 136
Stolz, W., see Spika 146 (1995) 521
Stringfellow, G.B., see Su 146 (1995) 558
Su, C.-H., see Sha 146 (1995) 42
Su, L.C., I.H. Ho and G.B. Stringfellow, Ordering in GaInP grown at low temperatures 146 (1995) 558
Sudjadi, U., see Spika 146 (1995) 521
Sulima, O.V., see Baldus 146 (1995) 299
Sulima, O.V., see Baldus 146 (1995) 305
Suzuki, T., see Kimata 146 (1995) 433
Symons, D.M., see Booker 146 (1995) 495
Szofran, F.R., see Sha 146 (1995) 42

Tabuchi, M., Y. Takeda, Y. Sakuraba, T. Kumamoto, K. Fujibayashi, I. Takahashi, J. Harada and H. Kamei, Atomic level interface structure of InP/InPAs/InP measured by X-ray crystal truncation rod scattering 146 (1995) 148
Tagwerker, M., W.M. Plotz and H. Sitter, Three-dimensional model calculations of epitaxial growth by Monte Carlo simulation 146 (1995) 22
Takahashi, I., see Tabuchi 146 (1995) 148

Takahashi, N., see Koukitu 146 (1995) 239
Takahashi, N., see Koukitu 146 (1995) 467
Takamiya, S., see Kizuki 146 (1995) 527
Takeda, Y., see Tabuchi 146 (1995) 148
Takeda, Y., see Fujiwara 146 (1995) 544
Takiguchi, H., M. Izawa, K. Yase, S. Ueno, M. Yoshimura, T. Yao and K. Sato, Molecular orientation of vapor-deposited films of long-chain molecules observed with atomic force microscopy 146 (1995) 645
Tanner, B.K., see Hallam 146 (1995) 604
Tansley, T.L., see Novikov 146 (1995) 34
Taudt, W., see Gurskii 146 (1995) 592
Tegude, F.J., see Prost 146 (1995) 538
Terekhov, A.S., see Bolkhovityanov 146 (1995) 31
Teterkina, I.V., see Chaldyshev 146 (1995) 246
Thomas, B., C. Höpfner, K. Ellmer, S. Fiechter and H. Tributsch, Growth of FeS_2 (pyrite) thin films on single crystalline substrates by low pressure metalorganic chemical vapour deposition 146 (1995) 63
Tillack, B., see Ritter 146 (1995) 119
Tokuda, T., see Nabetani 146 (1995) 363
Tomm, Y., R. Schieck, K. Ellmer and S. Fiechter, Growth mechanism and electronic properties of doped pyrite (FeS_2) crystals 146 (1995) 271
Tomm, Y., see Löher 146 (1995) 408
Torzo, G., see Rossetto 146 (1995) 511
Tournié, E., see Trampert 146 (1995) 368
Trampert, A., E. Tournié and K.H. Ploog, Defect control during growth of highly mismatched (100) InAs/GaAs-heterostructures 146 (1995) 368
Tributsch, H., see Thomas 146 (1995) 63
Trukhanov, E.M., see Bolkhovityanov 146 (1995) 31

Ueno, S., see Takiguchi 146 (1995) 645
Umeno, M., see Fujita 146 (1995) 384
Umeno, M., see Soga 146 (1995) 554
Utatsu, T., see Yano 146 (1995) 349
Uwaha, M., Y. Saito and M. Sato, Fluctuations and instabilities of steps in the growth and sublimation of crystals 146 (1995) 164

Vakarelska, K., see Gurskii 146 (1995) 592
Vasil'ev, M.G., see Kadinski 146 (1995) 209
Vedel, J., see Kampmann 146 (1995) 256
Vilisova, M.D., see Chaldyshev 146 (1995) 246
Völkl, J., see Rupp 146 (1995) 37
Volz, M.P., see Sha 146 (1995) 42

Wachtendorf, B., see Gurskii 146 (1995) 592
Wagner, G., see Steiner 146 (1995) 293
Wahid, A., see Gurskii 146 (1995) 592
Walker, P.J., see Booker 146 (1995) 495
Walter, T., see Nadeneau 146 (1995) 251
Watanabe, T., see Fujita 146 (1995) 384
Watanabe, T., see Nitatori 146 (1995) 389
Weber, J., see Gladkov 146 (1995) 319
Weidner, M., see Ritter 146 (1995) 119
Weinhold, V., see Hoffmann 146 (1995) 422
Weiß, S., see Spika 146 (1995) 521
Westwater, S., see Joyce 146 (1995) 394
Wettling, W., see Baldus 146 (1995) 299
Wettling, W., see Baldus 146 (1995) 305
Wetzel, G., see Rossberg 146 (1995) 112
Weyers, M., see Knauer 146 (1995) 549
Weyers, M., see Bergunde 146 (1995) 564
Wiedemeier, H., Y.R. Ge, M.A. Hutchins and Y.-G. Sha, Growth of $Hg_{1-x}Cd_xTe$ epitaxial layers on (100) CdTe by chemical vapor transport under normal and reduced gravity conditions 146 (1995) 61
Winnacker, A., see Hofmann 146 (1995) 214
Wirthl, E., H. Sitter and P. Bauer, Monocrystalline (100)-oriented ZnS layers grown on Si by molecular beam epitaxy 146 (1995) 404
Woitok, J., see Hövel 146 (1995) 515
Wojnowski, M., see Schönherr 146 (1995) 227

Yamamoto, K., see Yano 146 (1995) 349
Yamamoto, N., see Nabetani 146 (1995) 363
Yamazaki, S., see Fujii 146 (1995) 475
Yamazaki, S., see Fujii 146 (1995) 489
Yano, M., K. Yamamoto, T. Utatsu and M. Inoue, Time-resolved reflection high energy electron diffraction analysis for atomic layer depositions of GaSb by molecular beam epitaxy 146 (1995) 349
Yano, M., see Kimata 146 (1995) 433
Yao, H., see Schieber 146 (1995) 15
Yao, T., see Takiguchi 146 (1995) 645
Yase, K., see Takiguchi 146 (1995) 645
Yonezu, H., see Saitoh 146 (1995) 359
Yoshida, A., see Guo 146 (1995) 462
Yoshida, H., see Muranoi 146 (1995) 49
Yoshida, Y., see Ito 146 (1995) 655
Yoshimura, M., see Takiguchi 146 (1995) 645
Yu, T., see Chen 146 (1995) 624
Yuferev, V.S., see Kadinski 146 (1995) 209
Yumoto, H., see Gotoh 146 (1995) 198

Zanella, P., see Rossetto 146 (1995) 511
Zanotti, L., see Zha 146 (1995) 29
Zaumseil, P., see Ritter 146 (1995) 119
Zha, M., P. Franzosi, L. Zanotti, G. Zuccalli, C. Paorici, R. Capelletti and C. Razzetti, Crystal growth and characterisation of urea by physical vapour transport in semi-open cells 146 (1995) 29
Zimmermann, G., see Spika 146 (1995) 521
Zuccalli, G., see Zha 146 (1995) 29

Zweigart, S., D. Schmid, J. Kessler, H. Dittrich and H.W. Schock, Studies of the growth mechanism of polycrystalline $CuInSe_2$ thin films prepared by a sequential process 146 (1995) 233

Zytkiewicz, Z.R., Liquid phase electroepitaxial growth of thick and compositionally uniform AlGaAs layers on GaAs substrates 146 (1995) 283

ELSEVIER

Journal of Crystal Growth 146 (1995) 674–677

JOURNAL OF CRYSTAL GROWTH

Subject index

Adducts
– for aluminum gallium arsenide 515
Aluminum 503
– arsenide 344
– gallium arsenide 283, 299, 384, 399, 515, 521, 527, 564
– gallium nitride 455
– indium nitride 462
– nitride 503
– organic 503, 515, 521
Apparatus
– for thin film growth
– – by liquid phase epitaxy
– – – of gallium indium phosphide 287
– – by vapor phase epitaxy
– – – through chemical vapor deposition
– – – – of silicon carbide 37
– – – through metalorganic chemical vapor deposition
– – – – of lead titanate 624
– for vapor growth
– – by chemical transport
– – – of zinc selenide, substituted with transition metals 75
– for miscellaneous purposes
– – in situ gravimetric and optical methods in atomic layer epitaxy 467
– – X-ray analysis of metalorganic vapor phase epitaxy 104
Arsenic
– organic 521

Bismuth
– strontium calcium cuprate 659

Cadmium
– mercury telluride 610
– sulphide 59, 408
– sulphoselenide 414
– telluride 65, 92, 98, 125, 130, 136, 142, 256, 433
Calcium
– organic 599
– sulphide 599
Characterization
– by atomic force microscopy
– – of organic molecules 641, 645
– by detector spectra
– – of cadmium telluride 125
– by gamma-ray diffraction
– – of mercury(II) iodide 112
– by in situ monitoring of carbon doping
– – of gallium arsenide 394
– by in situ scanning electron microscopy
– – of molecular beam process 334
– by reflection high energy electron diffraction
– – of molecular beam epitaxy process 344, 349, 422
– by reflection supported pyrometric interferometry
– – of silicon–germanium 119
– by stress birefringence
– – of cadmium telluride 130
– by X-ray crystal truncation rod scattering
– – of indium pnectides 148
Computer simulation
– of compensation mechanism in cadmium telluride 142
– of growing steps 164
– of metalorganic chemical vapor deposition processes 202, 209
– of silicon carbide growth 214
Copper
– indium diselenide 233
– indium ditelluride 251
– phthalocyanine 641

Device characterization
– diodes 80, 455
– electronic materials 59, 92, 119, 125, 271, 444, 538
– heterojunction 80, 119, 153, 159, 287, 368, 384, 408, 418, 433, 439, 455, 533, 538
– lasers 159
– photoemitters 310
– quantum wells 159, 183, 379, 418, 422, 538
– radiation detectors 15
– solar cells 233, 256, 299, 305
Diffusional control
– of indium and tellurium across interface 433
– of mercury(II) iodide 9
Diodes, see Device characterization

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
– back, regrowth 299
– chemical 136, 293, 404, 527

Fullerene (C_{60}) 227

Gallium
– antimonide 87, 319, 349, 495
– arsenide 177, 183, 239, 246, 305, 326, 334, 344, 354, 359, 379, 389, 394, 467, 482, 521, 527, 564
– indium arsenide 489
– indium arsenide phosphide 287, 310
– indium nitride 455
– indium phosphide 558
– nitride 455
– organic 515, 521
– phosphide 554
– selenide 439
Gold 266

Heterojunction, see Device characterization

Indium
– arsenide 148, 363, 368, 374, 495
– gallium aluminum arsenide 159
– gallium arsenide 153, 533
– gallium arsenide phosphide 310
– nitride 262
– organic 511, 544
– phosphide 148, 171, 314, 475, 511, 533, 544, 549
– selenide 439
Iron
– disilicide 444
– disulphide 271, 630

Kinetics
– of growth 1, 9, 49, 119, 171, 177, 220, 227, 283, 326, 334, 344, 349, 363, 374, 482, 580, 599
– of interface control 379, 422, 527
– of lattice relaxation 489
– of nucleation 220, 326, 334, 344
– of selective area growth 475

Lasers, see Device characterization
Lead
– organic 624
– telluride 449
– tin telluride 69
– titanate 624

Melt growth technique
– by Czochralski method
– – of gallium antimonide 87
Mercury
– cadmium telluride 610, 619
– (II) iodide 1, 9, 15, 23, 112
– manganese telluride 604
– zinc selenide 427
Microgravity, growth under
– of cadmium telluride 98
– of mercury cadmium telluride 610
– of mercury(II) iodide 9
– of III–V compounds 171

Monte Carlo simulation
– of molecular beam epitaxy growth 220
Morphological stability
– of gallium arsenide 482
– of gold surface 266
– of silicon 293
– of steps 164
– of III–V compounds 171

Nonlinear optics, crystals for
– vanadyl phthalocyanine 649

Organic molecules 641, 645
Organic photoreceptor (DTPP) 636

Phase diagrams
– of indium/gallium/arsenic/phosphorus 310
– of mercury(II) iodide 15
Phosphorus
– organic 544
Precursor
– for aluminum 503
– for aluminum gallium arsenide 515, 521
– – doping of 399
– for aluminum nitride 503
– for calcium sulphide 599
– for gallium arsenide 521
– for indium phosphide 511
– for iron disilicide 444
– for zinc oxide 503
Purification of materials
– of arsenic (organic) precursor 521
Pyrite 271, 630

Quantum wells, see Device characterization

Selenium
– organic 580
Silicon 193, 293
– carbide 37, 214
– germanium 119
Silver 198
Solar cells, see Device characterization
Solution growth technique
– by electrodeposition
– – of cadmium telluride 256
– by flux method
– – of bismuth strontium calcium cuprate 659
Stoichiometry
– of mercury(II) iodide 15
Superconductivity materials, high T_c
– film
– – of BSCCO 659
– – of YBCO 655
Superlattices, multilayers
– of III–V compounds 389, 495

Surface structure
– of cadmium sulphide 408
– of indium arsenide 363, 374
– of iron disilicide 444
– of silicon 293

Thin film growth, epitaxy
– by atomic layer epitaxy
– – of gallium arsenide 239, 467
– by chemical beam epitaxy
– – of aluminum gallium arsenide 399
– – of gallium arsenide 394
– – of iron disilicide 444
– by hot wall epitaxy
– – of cadmium sulphoselenide 414
– by liquid phase electroepitaxy
– – of aluminum gallium arsenide 283
– – of III–V compounds 277
– by liquid phase epitaxy
– – of aluminum gallium arsenide 299
– – of bismuth strontium calcium cuprate 659
– – of gallium antimonide 319
– – of gallium arsenide 305
– – of gallium indium arsenide phosphide 287, 310
– – of indium gallium arsenide 153
– – of indium phosphide 314
– – of silicon 293
– – theory of 287
– by magnetron sputtering
– – of yttrium barium cuprate 655
– by metalorganic molecular beam epitaxy
– – of zinc telluride 587
– by molecular beam epitaxy
– – of aluminum arsenide 344
– – of aluminum gallium arsenide 384
– – of cadmium sulphide 408
– – of cadmium telluride 433
– – of gallium antimonide 349
– – of gallium arsenide 177, 326, 334, 344, 354, 359, 379, 389
– – of gallium selenide 439
– – of indium arsenide 363, 368, 374
– – of indium gallium aluminum arsenide 159
– – of indium selenide 439
– – of lead telluride 449
– – of mercury zinc selenide 427
– – of three (group) nitrides 340
– – of zinc magnesium selenide 418
– – of zinc manganese selenide 422
– – of zinc selenide 80, 422
– – of zinc sulphide 404
– – of zinc telluride 418
– – theory of 177, 220, 326, 449
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of gallium arsenide 246
– – – of mercury cadmium telluride 610
– – – of silicon carbide 37
– – – of silicon–germanium 119
– – through evaporation and condensation
– – – of copper indium diselenide 233
– – – of copper indium ditelluride 251
– – – of gold 266
– – – of indium nitride 262
– – – of organic molecules 641, 645, 649
– – – of organic photoreceptor (DTPP) 636
– – – theory of 198
– – through metalorganic chemical vapor deposition
– – – of aluminum 503
– – – of aluminum gallium arsenide 515, 521, 527, 564
– – – of aluminum gallium nitride 455
– – – of aluminum indium nitride 462
– – – of aluminum nitride 503
– – – of calcium sulphide 599
– – – of gallium antimonide 495
– – – of gallium arsenide 183, 379, 482, 521, 527, 564
– – – of gallium indium arsenide 489
– – – of gallium indium nitride 455
– – – of gallium indium phosphide 558
– – – of gallium nitride 455
– – – of gallium phosphide 554
– – – of indium arsenide 148, 495
– – – of indium gallium arsenide 533
– – – of indium phosphide 148, 475, 511, 533, 544, 549
– – – of iron disulphide 630
– – – of lead titanate 624
– – – of mercury cadmium telluride 619
– – – of mercury manganese telluride 604
– – – of III–V compounds 538
– – – of II–VI compounds 570
– – – of zinc oxide 503
– – – of zinc selenide 580, 592
– – – theory of 183, 202, 209
– theory of 193
Three–five (III–V) compounds 171, 277, 389, 495, 538
– review of 277
Three(III)-nitrides 340
Titanium
– nitride 188
– organic 624
n-Tritriacontane 641
Two–six (II–VI) compounds
– review of 570

Urea 29

Vanadyl
– phthalocyanine 649
Vapor growth technique
– by chemical transport
– – of iron disulphide 271
– – of titanium nitride 188
– – of zinc selenide 53, 75
– by "contactless" method
– – of cadmium sulphide 59
– – of cadmium telluride 65

– by evaporation and condensation
– – of cadmium telluride 92, 98, 125, 130, 142
– – of fullerene 227
– – of lead tin telluride 69
– – of mercury(II) iodide 1, 9, 15, 23, 112
– – of silicon carbide 214
– – of urea 29
– – of zinc selenide 42, 49
– – theory of 214
– theory of 164

Yttrium
– barium cuprate 655

Zinc
– magnesium selenide 418
– manganese selenide 422
– organic 503
– oxide 503
– selenide 42, 49, 53, 75, 80, 422, 580, 592
– sulphide 404
– telluride 418, 587